

DRAM MODULE

MT8D432(X)
MT16D832(X)

FEATURES

- JEDEC- and industry-standard pinout in a 72-pin, single in-line memory module (SIMM)
- 16MB (4 Meg x 32) and 32MB (8 Meg x 32)
- High-performance CMOS silicon-gate process
- Single 5V $\pm 10\%$ power supply
- All inputs, outputs and clocks are TTL-compatible
- Refresh modes: RAS#-ONLY, CAS#-BEFORE-RAS# (CBR) and HIDDEN
- 2,048-cycle refresh distributed across 32ms
- FAST PAGE MODE (FPM) operating mode or Extended Data-Out (EDO) PAGE MODE operating mode

OPTIONS

- Timing
50ns access
60ns access
- Packages
72-pin SIMM
72-pin SIMM (gold)
- Operating Modes
FAST PAGE MODE
EDO PAGE MODE

*EDO version only

MARKING

-5*

-6

M

G

Blank

X

PART NUMBERS

EDO Operating Mode

PART NUMBER	CONFIGURATION	PLATING
MT8D432G- xx X	4 Meg x 32	Gold
MT8D432M- xx X	4 Meg x 32	Tin/Lead
MT16D832G-xx X	8 Meg x 32	Gold
MT16D832M-xx X	8 Meg x 32	Tin/Lead

xx = speed

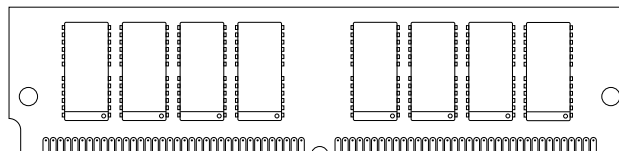
FPM Operating Mode

PART NUMBER	CONFIGURATION	PLATING
MT8D432G-xx	4 Meg x 32	Gold
MT8D432M-xx	4 Meg x 32	Tin/Lead
MT16D832G-xx	8 Meg x 32	Gold
MT16D832M-xx	8 Meg x 32	Tin/Lead

xx = speed

PIN ASSIGNMENT (Front View)

72-Pin SIMM
(DD-3) 4 Meg x 32
(DD-4) 8 Meg x 32



PIN	SYMBOL	PIN	SYMBOL	PIN	SYMBOL	PIN	SYMBOL
1	Vss	19	A10	37	NC	55	DQ12
2	DQ1	20	DQ5	38	NC	56	DQ28
3	DQ17	21	DQ21	39	Vss	57	DQ13
4	DQ2	22	DQ6	40	CAS0#	58	DQ29
5	DQ18	23	DQ22	41	CAS2#	59	Vcc
6	DQ3	24	DQ7	42	CAS3#	60	DQ30
7	DQ19	25	DQ23	43	CAS1	61	DQ14
8	DQ4	26	DQ8	44	RAS0#	62	DQ31
9	DQ20	27	DQ24	45	NC/RAS1#*	63	DQ15
10	Vcc	28	A7	46	NC	64	DQ32
11	NC	29	NC (A11)	47	WE#	65	DQ16
12	A0	30	Vcc	48	NC	66	NC
13	A1	31	A8	49	DQ9	67	PRD1
14	A2	32	A9	50	DQ25	68	PRD2
15	A3	33	NC/RAS3#*	51	DQ10	69	PRD3
16	A4	34	RAS2#	52	DQ26	70	PRD4
17	A5	35	NC	53	DQ11	71	NC
18	A6	36	NC	54	DQ27	72	Vss

*32MB version only

NOTE: Symbols in parentheses are not used on these modules but may be used for other modules in this product family. They are for reference only.

KEY TIMING PARAMETERS

EDO Operating Mode

SPEED	t _{RC}	t _{RAC}	t _{PC}	t _{AA}	t _{CAC}	t _{CAS}
-5	84ns	50ns	20ns	25ns	13ns	8ns
-6	104ns	60ns	25ns	30ns	15ns	10ns

FPM Operating Mode

SPEED	t _{RC}	t _{RAC}	t _{PC}	t _{AA}	t _{CAC}	t _{RP}
-6	110ns	60ns	35ns	30ns	15ns	40ns

GENERAL DESCRIPTION

The MT8D432(X) and MT16D832(X) are randomly accessed 16MB and 32MB solid-state memories organized in a x32 configuration. During READ or WRITE cycles, each bit is uniquely addressed through the 22 address bits, which are entered 11 bits (A0-A10) at a time. RAS# is used to latch the first 11 bits and CAS# the latter 11 bits. READ and WRITE cycles are selected with the WE# input. A logic HIGH on WE# dictates READ mode while a logic LOW on WE# dictates WRITE mode. During a WRITE cycle, data-in (D) is latched by the falling edge of CAS#. Since WE# goes LOW prior to CAS# going LOW, the output pin(s) remain open (High-Z) until the next CAS# cycle.

FAST PAGE MODE

FAST PAGE MODE operations allow faster data operations (READ or WRITE) within a row-address-defined page boundary. The FAST PAGE MODE cycle is always initiated with a row address strobed-in by RAS# followed by a column address strobed-in by CAS#. CAS# may be toggled in by holding RAS# LOW and strobing-in different column addresses, thus executing faster memory cycles. Returning RAS# HIGH terminates the FAST PAGE MODE operation.

EDO PAGE MODE

EDO PAGE MODE, designated by the "X" version, is an accelerated FAST PAGE MODE cycle. The primary advantage of EDO is the availability of data-out even after CAS# goes back HIGH. EDO provides for CAS# precharge time

(^tCP) to occur without the output data going invalid. This elimination of CAS# output control provides for pipeline READs.

FAST PAGE MODE modules have traditionally turned the output buffers off (High-Z) with the rising edge of CAS#. EDO operates like FAST-PAGE-MODE READs, except data will be held valid or become valid after CAS# goes HIGH, as long as RAS# and OE# are held LOW. (Reference MT4C4M4E8 DRAM data sheet for additional information on EDO functionality.)

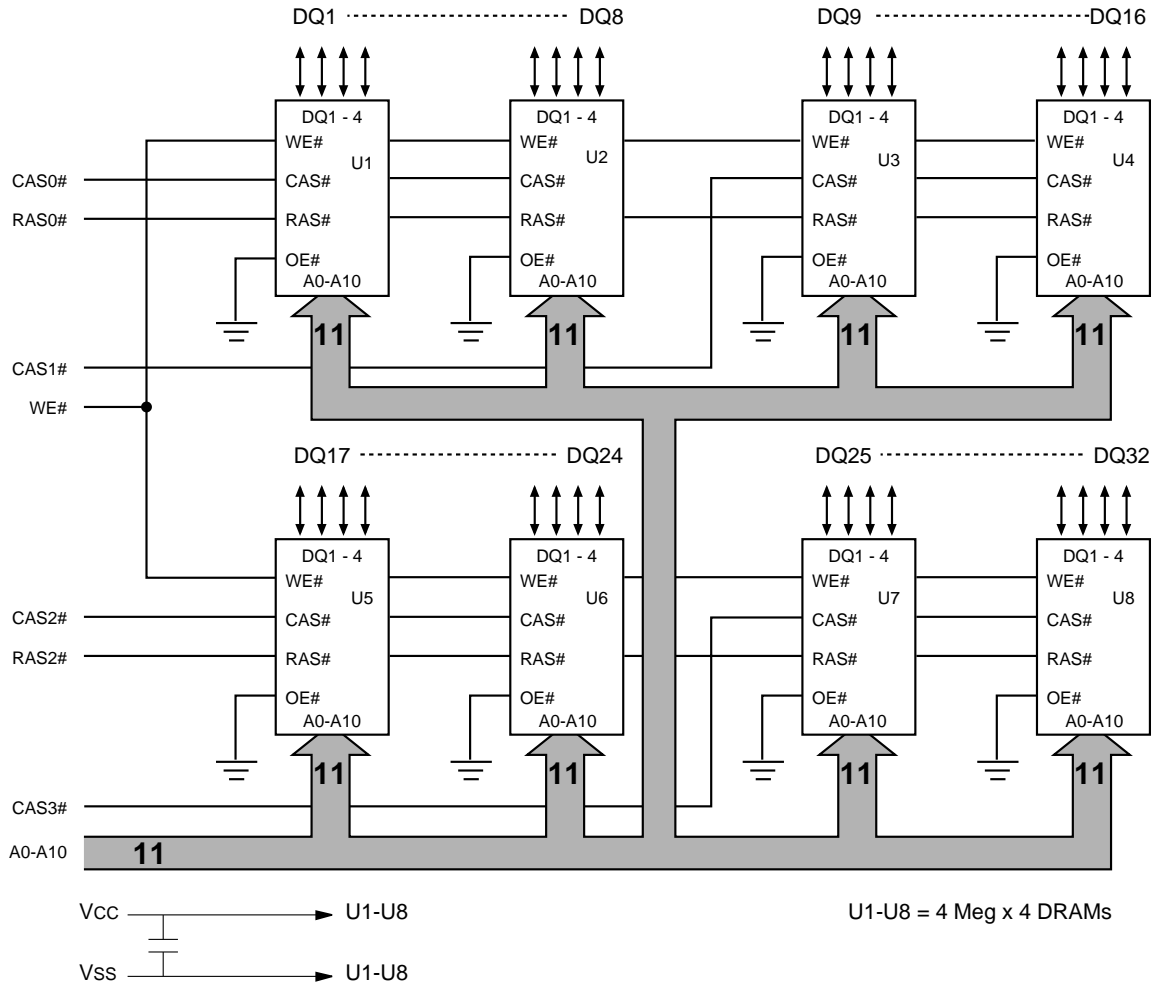
REFRESH

Returning RAS# and CAS# HIGH terminates a memory cycle and decreases chip current to a reduced standby level. Also, the chip is preconditioned for the next cycle during the RAS# HIGH time. Memory cell data is retained in its correct state by maintaining power and executing any RAS# cycle (READ, WRITE) or RAS# refresh cycle (RAS#-ONLY, CBR or HIDDEN) so that all 2,048 combinations of RAS# addresses are executed at least every 32ms, regardless of sequence. The CBR REFRESH cycle will invoke the refresh counter for automatic RAS# addressing.

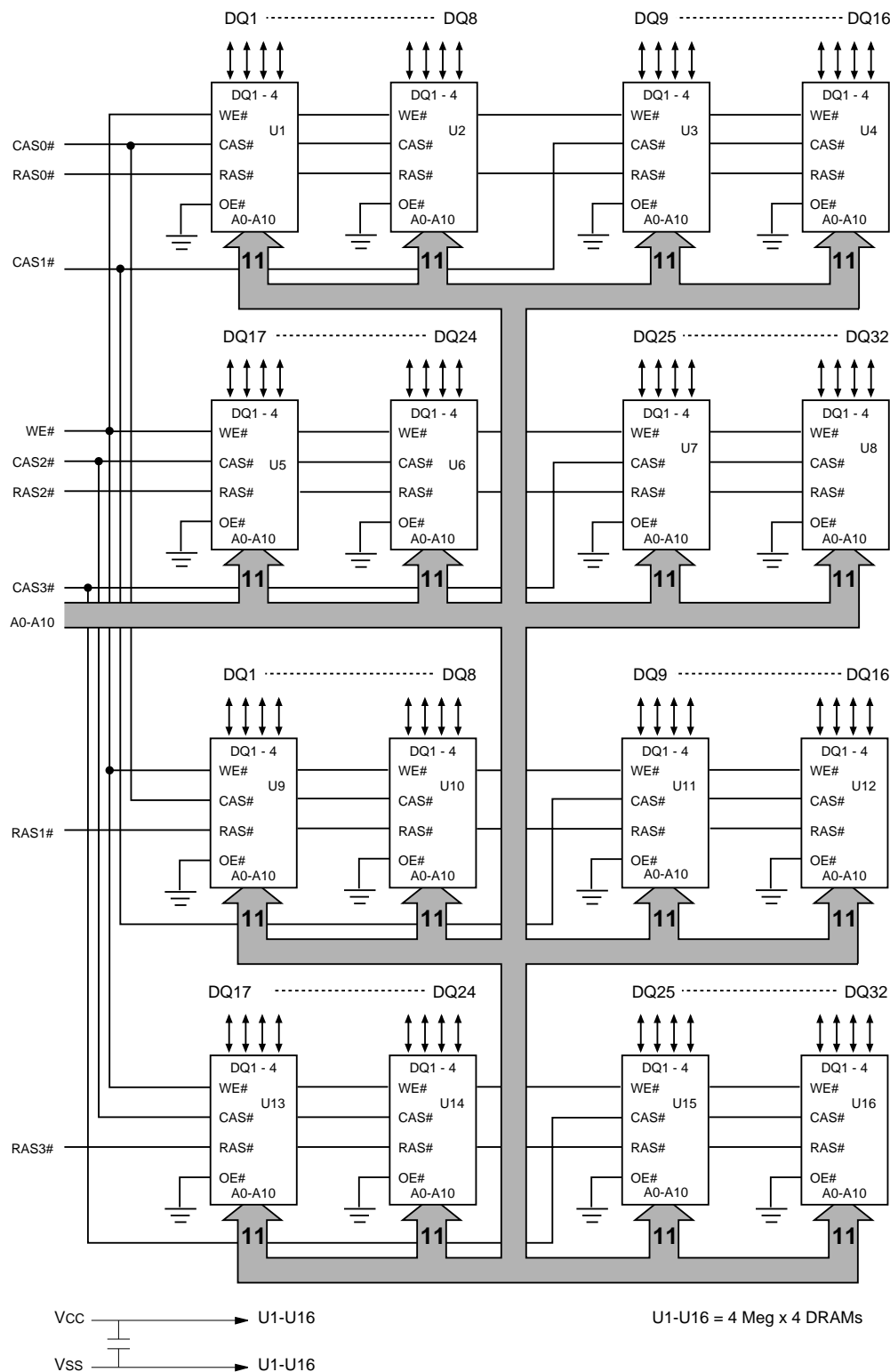
x16 CONFIGURATION

For x16 applications, the corresponding DQ and CAS# pins must be connected together (DQ1 to DQ17, DQ2 to DQ18 and so forth, and CAS0# to CAS2# and CAS1# to CAS3#). Each RAS# is then a bank select for the x16 memory organization.

**FUNCTIONAL BLOCK DIAGRAM
MT8D432(X) (16MB)**



**FUNCTIONAL BLOCK DIAGRAM
MT16D832(X) (32MB)**



TRUTH TABLE

FUNCTION		RAS#	CAS#	WE#	ADDRESSES		DATA-IN/OUT
					t _R	t _C	DQ1-DQ32
Standby		H	H→X	X	X	X	High-Z
READ		L	L	H	ROW	COL	Data-Out
EARLY WRITE		L	L	L	ROW	COL	Data-In
EDO/FAST-PAGE-MODE READ	1st Cycle	L	H→L	H	ROW	COL	Data-Out
	2nd Cycle	L	H→L	H	n/a	COL	Data-Out
EDO/FAST-PAGE-MODE EARLY-WRITE	1st Cycle	L	H→L	L	ROW	COL	Data-In
	2nd Cycle	L	H→L	L	n/a	COL	Data-In
	Any Cycle (X version)	L	L→H	H	n/a	n/a	Data-Out
RAS#-ONLY REFRESH		L	H	X	ROW	n/a	High-Z
HIDDEN REFRESH	READ	L→H→L	L	H	ROW	COL	Data-Out
	WRITE	L→H→L	L	L	ROW	COL	Data-In
CBR REFRESH		H→L	L	H	X	X	High-Z

**JEDEC-DEFINED
 PRESENCE-DETECT – MT8D432(X) (16MB)**

SYMBOL	PIN	-5*	-6
PRD1	67	V _{SS}	V _{SS}
PRD2	68	NC	NC
PRD3	69	V _{SS}	NC
PRD4	70	V _{SS}	NC

**JEDEC-DEFINED
 PRESENCE-DETECT – MT16D832(X) (32MB)**

SYMBOL	PIN	-5*	-6
PRD1	67	NC	NC
PRD2	68	V _{SS}	V _{SS}
PRD3	69	V _{SS}	NC
PRD4	70	V _{SS}	NC

*EDO version only

ABSOLUTE MAXIMUM RATINGS*

Voltage on Any Pin Relative to V_{SS} -1V to +7V
 Operating Temperature, T_A (ambient) 0°C to +70°C
 Storage Temperature (plastic) -55°C to +125°C
 Power Dissipation 8W
 Short Circuit Output Current 50mA

*Stresses greater than those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

DC ELECTRICAL CHARACTERISTICS AND OPERATING CONDITIONS

(Notes: 1) (V_{CC} = +5V ±10%)

PARAMETER/CONDITION		SYMBOL	MIN	MAX	UNITS	NOTES
Supply Voltage		V _{CC}	4.5	5.5	V	
Input High (Logic 1) Voltage, all inputs		V _{IH}	2.0	5.5	V	
Input Low (Logic 0) Voltage, all inputs		V _{IL}	-1.0	0.8	V	
INPUT LEAKAGE CURRENT Any input 0V ≤ V _{IN} ≤ 5.5V (All other pins not under test = 0V)	RAS0#-RAS3#	I _{I1}	-8	8	μA	
	A0-A10, WE#	I _{I2}	-32	32	μA	23
	CAS0#-CAS3#	I _{I3}	-8	8	μA	23
OUTPUT LEAKAGE CURRENT (DQ is disabled; 0V ≤ V _{OUT} ≤ 5.5V)	DQ1-DQ32	I _{OZ}	-10	10	μA	23
OUTPUT LEVELS Output High Voltage (I _{OUT} = -5mA) Output Low Voltage (I _{OUT} = 4.2mA)		V _{OH}	2.4		V	
		V _{OL}		0.4	V	

I_{CC} OPERATING CONDITIONS AND MAXIMUM LIMITS

(Notes: 1, 5, 6) (V_{CC} = +5V ±10%)

PARAMETER/CONDITION	SYMBOL	SIZE	MAX		UNITS	NOTES
			-5*	-6		
STANDBY CURRENT: (TTL) (RAS# = CAS# = V _{IH})	I _{CC1}	16MB 32MB	18 36	18 36	mA	
STANDBY CURRENT: (CMOS) (RAS# = CAS# = other inputs = V _{CC} -0.2V)	I _{CC2}	16MB 32MB	14 28	14 28	mA	
OPERATING CURRENT: Random READ/WRITE Average power supply current (RAS#, CAS#, address cycling: t _{RC} = t _{RC} [MIN])	I _{CC3}	16MB 32MB	880 898	800 818	mA	3, 22
OPERATING CURRENT: FAST PAGE MODE Average power supply current (RAS# = V _{IL} , CAS#, address cycling: t _{PC} = t _{PC} [MIN])	I _{CC4}	16MB 32MB	- -	640 666	mA	3, 22
OPERATING CURRENT: EDO PAGE MODE Average power supply current (RAS# = V _{IL} , CAS#, address cycling: t _{PC} = t _{PC} [MIN])	I _{CC5} (X only)	16MB 32MB	880 898	800 818	mA	3, 22
REFRESH CURRENT: RAS#-ONLY Average power supply current (RAS# cycling, CAS# = V _{IH} : t _{RC} = t _{RC} [MIN])	I _{CC6}	16MB 32MB	880 898	800 818	mA	3, 22
REFRESH CURRENT: CBR Average power supply current (RAS#, CAS#, address cycling: t _{RC} = t _{RC} [MIN])	I _{CC7}	16MB 32MB	880 898	800 818	mA	3, 4

*EDO version only

CAPACITANCE

PARAMETER	SYMBOL	MAX		UNITS	NOTES
		16MB	32MB		
Input Capacitance: A0-A10	C _{I1}	48	95	pF	2
Input Capacitance: WE#	C _{I2}	64	127	pF	2
Input Capacitance: RAS0# - RAS3#	C _{I3}	32	32	pF	2
Input Capacitance: CAS0# - CAS3#	C _{I4}	16	32	pF	2
Input/Output Capacitance: DQ1-DQ32	C _{IO}	10	16	pF	2

FAST PAGE MODE

AC ELECTRICAL CHARACTERISTICS

(Notes: 5, 6, 7, 8, 9, 10, 11, 12) ($V_{CC} = +5V \pm 10\%$)

AC CHARACTERISTICS - FAST PAGE MODE OPTION		-6			
PARAMETER	SYM	MIN	MAX	UNITS	NOTES
Access time from column address	t_{AA}		30	ns	
Column-address hold time (referenced to RAS#)	t_{AR}	45		ns	
Column-address setup time	t_{ASC}	0		ns	
Row-address setup time	t_{ASR}	0		ns	
Access time from CAS#	t_{CAC}		15	ns	
Column-address hold time	t_{CAH}	10		ns	
CAS# pulse width	t_{CAS}	15	10,000	ns	
CAS# hold time (CBR REFRESH)	t_{CHR}	10		ns	4
CAS# to output in Low-Z	t_{CLZ}	3		ns	21
CAS# precharge time	t_{CP}	10		ns	13
Access time from CAS# precharge	t_{CPA}		35	ns	
CAS# to RAS# precharge time	t_{CRP}	5		ns	
CAS# hold time	t_{CSH}	60		ns	
CAS# setup time (CBR REFRESH)	t_{CSR}	5		ns	4
Write command to CAS# lead time	t_{CWL}	15		ns	
Data-in hold time	t_{DH}	10		ns	18
Data-in setup time	t_{DS}	0		ns	18
Output buffer turn-off delay	t_{OFF}	3	15	ns	17, 21
FAST-PAGE-MODE READ or WRITE cycle time	t_{PC}	35		ns	
Access time from RAS#	t_{RAC}		60	ns	
RAS# to column-address delay time	t_{RAD}	15		ns	15
Row-address hold time	t_{RAH}	10		ns	
RAS# pulse width	t_{RAS}	60	10,000	ns	
RAS# pulse width (FAST PAGE MODE)	t_{RASP}	60	125,000	ns	
Random READ or WRITE cycle time	t_{RC}	110		ns	
RAS# to CAS# delay time	t_{RCD}	20		ns	14
Read command hold time (referenced to CAS#)	t_{RCH}	0		ns	16
Read command setup time	t_{RCS}	0		ns	
Refresh period (2,048 cycles)	t_{REF}		32	ms	
RAS# precharge time	t_{RP}	40		ns	
RAS# to CAS# precharge time	t_{RPC}	0		ns	
Read command hold time (referenced to RAS#)	t_{RRH}	0		ns	16
RAS# hold time	t_{RSH}	15		ns	
Write command to RAS# lead time	t_{RWL}	15		ns	
Transition time (rise or fall)	t_T	2	50	ns	
Write command hold time	t_{WCH}	10		ns	
Write command hold time (referenced to RAS#)	t_{WCR}	45		ns	
WE# command setup time	t_{WCS}	0		ns	
Write command pulse width	t_{WP}	10		ns	
WE# hold time (CBR REFRESH)	t_{WRH}	10		ns	
WE# setup time (CBR REFRESH)	t_{WRP}	10		ns	

EDO PAGE MODE

AC ELECTRICAL CHARACTERISTICS

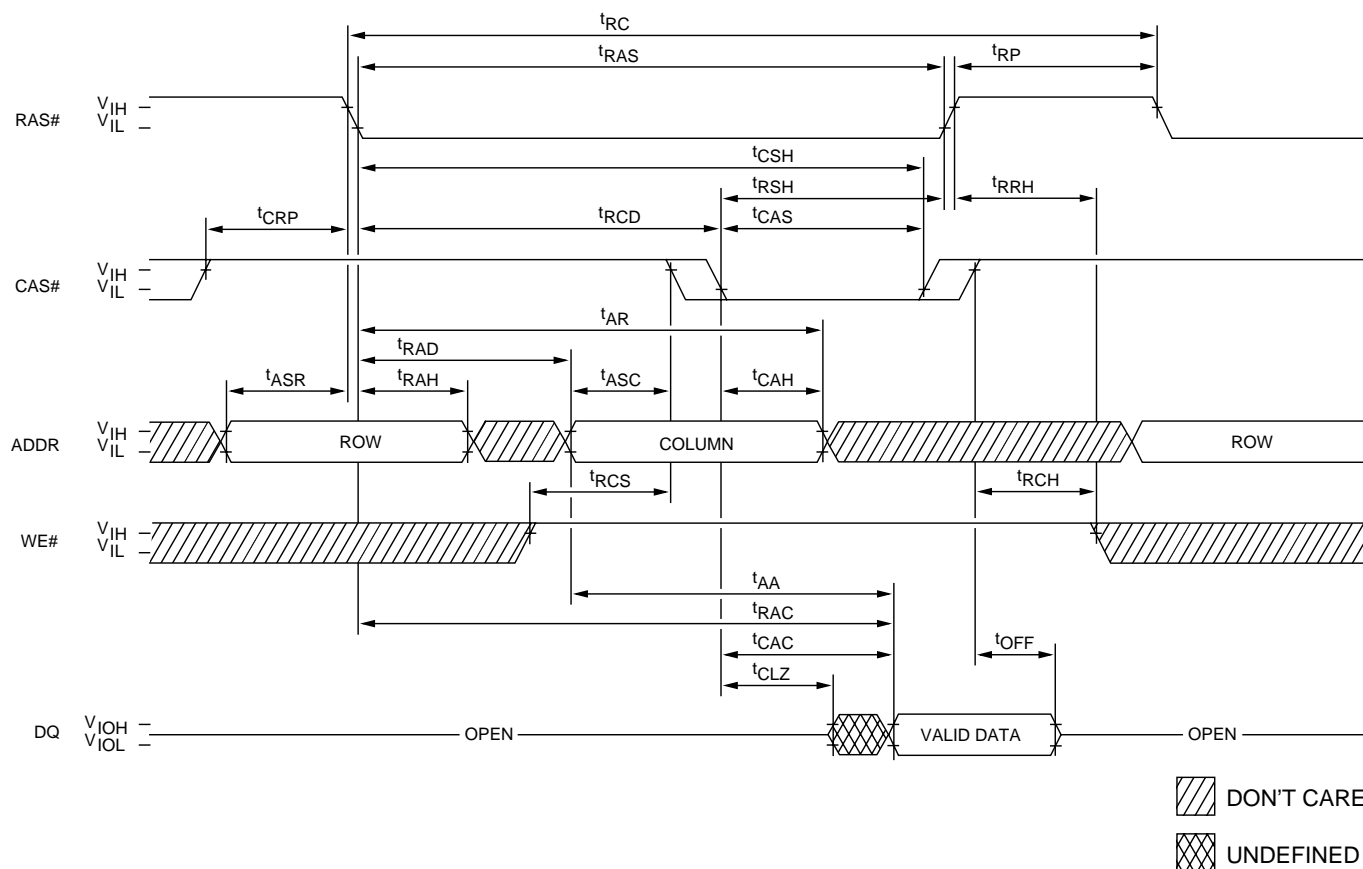
(Notes: 5, 6, 7, 8, 9, 10, 11, 12) ($V_{CC} = +5V \pm 10\%$)

AC CHARACTERISTICS - EDO PAGE MODE OPTION		-5		-6		UNITS	NOTES
PARAMETER	SYM	MIN	MAX	MIN	MAX		
Access time from column address	t_{AA}		25		30	ns	
Column-address set-up to CAS# precharge	t_{ACH}	12		15		ns	
Column-address hold time (referenced to RAS#)	t_{AR}	38		45		ns	
Column-address setup time	t_{ASC}	0		0		ns	
Row-address setup time	t_{ASR}	0		0		ns	
Access time from CAS#	t_{CAC}		13		15	ns	
Column-address hold time	t_{CAH}	8		10		ns	
CAS# pulse width	t_{CAS}	8	10,000	10	10,000	ns	
CAS# hold time (CBR REFRESH)	t_{CHR}	8		10		ns	4
CAS# to output in Low-Z	t_{CLZ}	0		0		ns	
Data output hold after next CAS# LOW	t_{COH}	3		3		ns	
CAS# precharge time	t_{CP}	8		10		ns	13
Access time from CAS# precharge	t_{CPA}		28		35	ns	
CAS# to RAS# precharge time	t_{CRP}	5		5		ns	
CAS# hold time	t_{CSH}	38		45		ns	
CAS# setup time (CBR REFRESH)	t_{CSR}	5		5		ns	4
Write command to CAS# lead time	t_{CWL}	8		10		ns	
Data-in hold time	t_{DH}	8		10		ns	18
Data-in setup time	t_{DS}	0		0		ns	18
Output buffer turn-off delay	t_{OFF}	0	12	0	15	ns	17, 21
EDO-PAGE-MODE READ or WRITE cycle time	t_{PC}	20		25		ns	
Access time from RAS#	t_{RAC}		50		60	ns	
RAS# to column-address delay time	t_{RAD}	9		12		ns	15
Row-address hold time	t_{RAH}	9		10		ns	
RAS# pulse width	t_{RAS}	50	10,000	60	10,000	ns	
RAS# pulse width (EDO PAGE MODE)	t_{RASP}	50	125,000	60	125,000	ns	
Random READ or WRITE cycle time	t_{RC}	84		104		ns	
RAS# to CAS# delay time	t_{RCD}	11		14		ns	14
Read command hold time (referenced to CAS#)	t_{RCH}	0		0		ns	16
Read command setup time	t_{RCS}	0		0		ns	
Refresh period (2,048 cycles)	t_{REF}		32		32	ms	
RAS# precharge time	t_{RP}	30		40		ns	
RAS# to CAS# precharge time	t_{RPC}	5		5		ns	
Read command hold time (referenced to RAS#)	t_{RRH}	0		0		ns	16
RAS# hold time	t_{RSH}	13		15		ns	
Write command to RAS# lead time	t_{RWL}	13		15		ns	
Transition time (rise or fall)	t_T	2	50	2	50	ns	
Write command hold time	t_{WCH}	8		10		ns	
Write command hold time (referenced to RAS#)	t_{WCR}	38		45		ns	
WE# command setup time	t_{WCS}	0		0		ns	
Output disable delay from WE#	t_{WHZ}	0	12	0	15	ns	
Write command pulse width	t_{WP}	5		5		ns	
WE# pulse to disable at CAS# HIGH	t_{WPZ}	10		10		ns	
WE# hold time (CBR REFRESH)	t_{WRH}	8		10		ns	
WE# setup time (CBR REFRESH)	t_{WRP}	8		10		ns	

NOTES

1. All voltages referenced to V_{SS}.
2. This parameter is sampled. Capacitance is measured using MIL-STD-883C, Method 3012.1 (1 MHz AC, V_{CC} = 4.5V, DC bias = 2.4V at 15mV RMS).
3. I_{CC} is dependent on output loading and cycle rates. Specified values are obtained with minimum cycle time and the outputs open.
4. Enables on-chip refresh and address counters.
5. The minimum specifications are used only to indicate cycle time at which proper operation over the full temperature range is ensured.
6. An initial pause of 100μs is required after power-up, followed by eight RAS# refresh cycles (RAS#-ONLY or CBR with WE# HIGH), before proper device operation is ensured. The eight RAS# cycle wake-ups should be repeated any time the t_{REF} refresh requirement is exceeded.
7. AC characteristics assume t_T = 5ns for FAST PAGE MODE and t_T = 2.5ns for EDO PAGE MODE.
8. V_{IH} (MIN) and V_{IL} (MAX) are reference levels for measuring timing of input signals. Transition times are measured between V_{IH} and V_{IL} (or between V_{IL} and V_{IH}).
9. In addition to meeting the transition rate specification, all input signals must transit between V_{IH} and V_{IL} (or between V_{IL} and V_{IH}) in a monotonic manner.
10. If CAS# = V_{IH}, data output is High-Z.
11. If CAS# = V_{IL}, data output may contain data from the last valid READ cycle.
12. Measured with a load equivalent to two TTL gates and 100pF, V_{OL} = 0.8V and V_{OH} = 2V.
13. If CAS# is LOW at the falling edge of RAS#, Q will be maintained from the previous cycle. To initiate a new cycle and clear the data-out buffer, CAS# must be pulsed HIGH for t_{CP}.
14. The t_{RCD} (MAX) limit is no longer specified. t_{RCD} (MAX) was specified as a reference point only. If t_{RCD} was greater than the specified t_{RCD} (MAX) limit, then access time was controlled exclusively by t_{CAC} (t_{RAC} [MIN] no longer applied). With or without the t_{RCD} (MAX) limit, t_{AA} and t_{CAC} must always be met.
15. The t_{RAD} (MAX) limit is no longer specified. t_{RAD} (MAX) was specified as a reference point only. If t_{RAD} was greater than the specified t_{RAD} (MAX) limit, then access time was controlled exclusively by t_{AA} (t_{RAC} and t_{CAC} no longer applied). With or without the t_{RAD} (MAX) limit, t_{AA}, t_{RAC} and t_{CAC} must always be met.
16. Either t_{RCH} or t_{RRH} must be satisfied for a READ cycle.
17. t_{OFF} (MAX) defines the time at which the output achieves the open circuit condition and is not referenced to V_{OH} or V_{OL}.
18. These parameters are referenced to CAS# leading edge in EARLY WRITE cycles.
19. OE# is tied permanently LOW; LATE WRITE or READ-MODIFY-WRITE operations are not permissible and should not be attempted.
20. A HIDDEN REFRESH may also be performed after a WRITE cycle. In this case, WE# = LOW and OE# = HIGH.
21. The 3ns minimum is a parameter guaranteed by design.
22. Column address changed once each cycle.
23. 16MB module values will be half of those shown.
24. For FAST PAGE MODE option, t_{OFF} is determined by the first RAS# or CAS# signal to transition HIGH. In comparison, t_{OFF} on an EDO option is determined by the latter of the RAS# and CAS# signal to transition HIGH.
25. Applies to both EDO and FAST PAGE MODE modules.

READ CYCLE (FAST PAGE MODE Module)

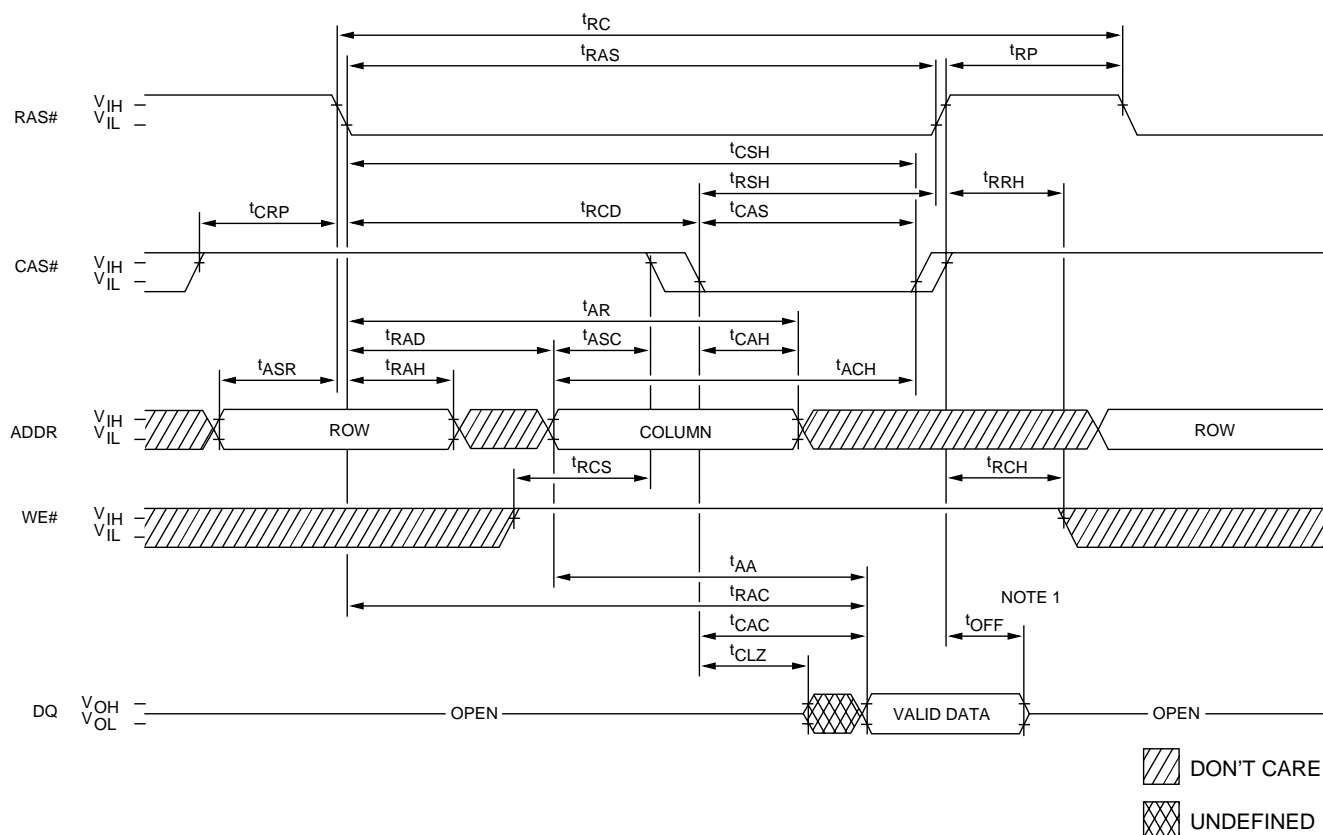


FAST PAGE MODE TIMING PARAMETERS

SYMBOL	-6		UNITS
	MIN	MAX	
t _{AA}		30	ns
t _{AR}	45		ns
t _{ASC}	0		ns
t _{ASR}	0		ns
t _{CAC}		15	ns
t _{CAH}	10		ns
t _{CAS}	15	10,000	ns
t _{CLZ}	3		ns
t _{CRP}	5		ns
t _{CSH}	60		ns
t _{OFF}	3	15	ns

SYMBOL	-6		UNITS
	MIN	MAX	
t _{RAC}		60	ns
t _{RAD}	15		ns
t _{RAH}	10		ns
t _{RAS}	60	10,000	ns
t _{RC}	110		ns
t _{RCD}	20		ns
t _{RCH}	0		ns
t _{RCS}	0		ns
t _{RP}	40		ns
t _{RRH}	0		ns
t _{RSH}	15		ns

READ CYCLE (EDO PAGE MODE Module)



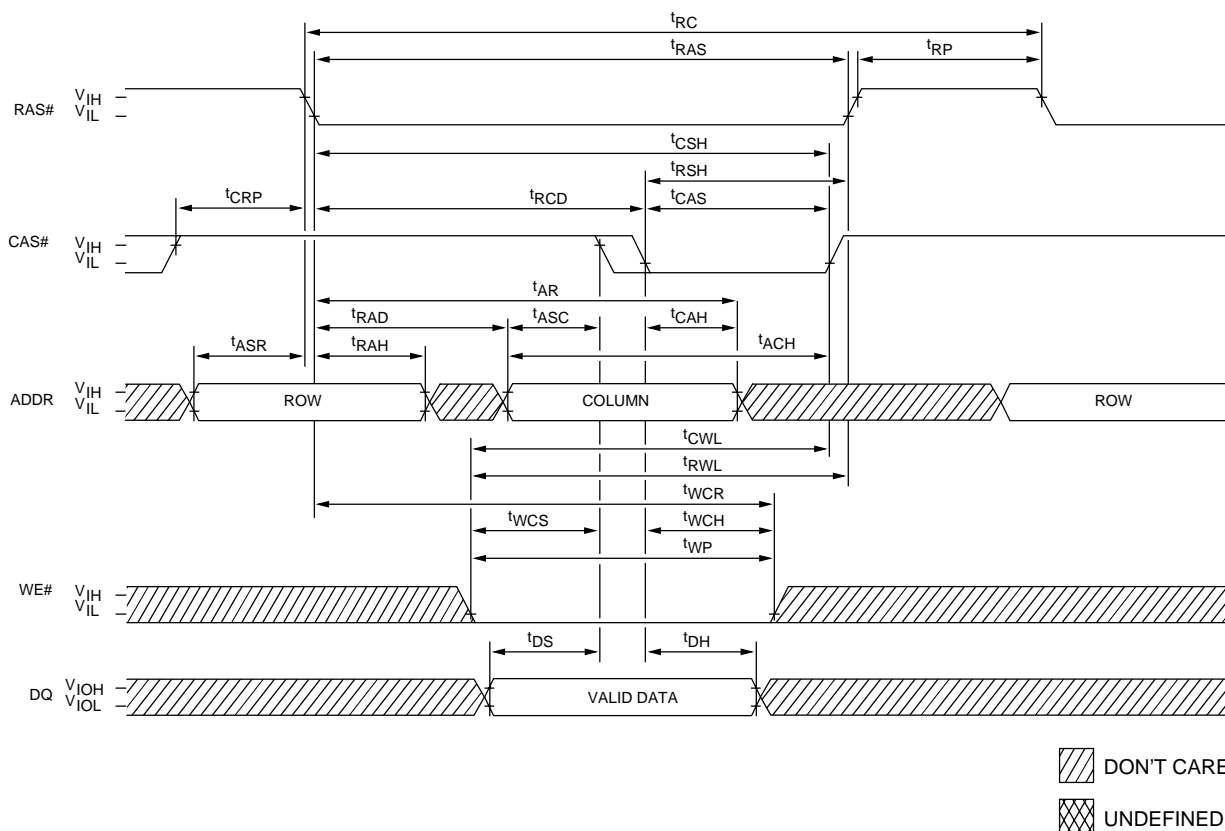
EDO PAGE MODE TIMING PARAMETERS

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{AA}		25		30	ns
t _{AR}	38		45		ns
t _{ASC}	0		0		ns
t _{ASR}	0		0		ns
t _{CAC}		13		15	ns
t _{CAH}	8		10		ns
t _{CAS}	8	10,000	10	10,000	ns
t _{CLZ}	0		0		ns
t _{CRP}	5		5		ns
t _{CSH}	38		45		ns
t _{OFF}	0	12	0	15	ns

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{RAC}		50		60	ns
t _{RAD}	9		12		ns
t _{RAH}	9		10		ns
t _{RAS}	50	10,000	60	10,000	ns
t _{RC}	84		104		ns
t _{RCD}	11		14		ns
t _{RCH}	0		0		ns
t _{RCS}	0		0		ns
t _{RP}	30		40		ns
t _{RRH}	0		0		ns
t _{RSH}	13		15		ns

NOTE: 1. t_{OFF} is referenced from rising edge of RAS# or CAS#, whichever occurs last.

EARLY WRITE CYCLE ²⁵



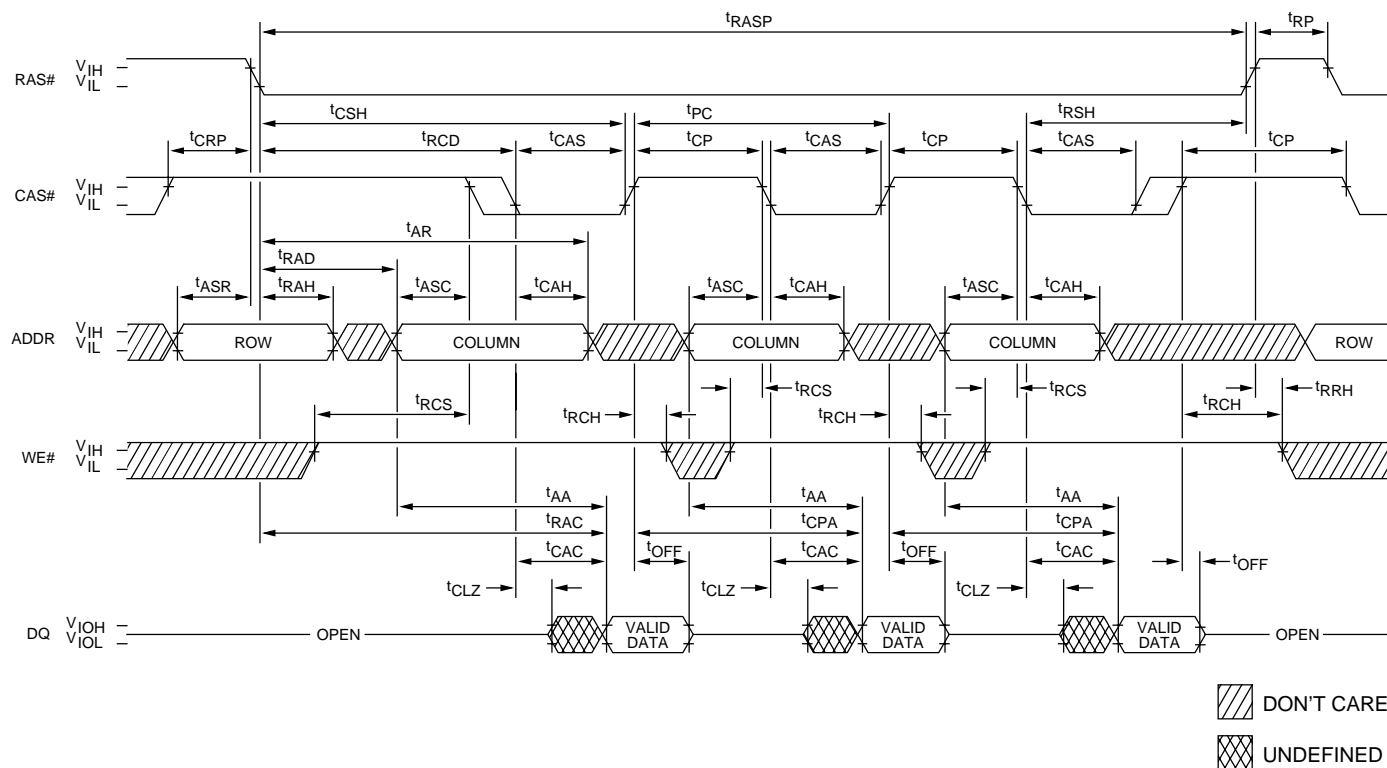
FAST PAGE MODE AND EDO PAGE MODE TIMING PARAMETERS

SYMBOL	-5*		-6		UNITS
	MIN	MAX	MIN	MAX	
t_{ACH} (EDO)	12		15		ns
t_{AR}	38		45		ns
t_{ASC}	0		0		ns
t_{ASR}	0		0		ns
t_{CAH}	8		10		ns
t_{CAS} (FPM)	—	—	15	10,000	ns
t_{CAS} (EDO)	8	10,000	10	10,000	ns
t_{CRP}	5		5		ns
t_{CSH} (FPM)	—		60		ns
t_{CSH} (EDO)	38		45		ns
t_{CWL} (FPM)	—		15		ns
t_{CWL} (EDO)	8		10		ns
t_{DH}	8		10		ns
t_{DS}	0		0		ns
t_{RAD} (FPM)	—		15		ns

SYMBOL	-5*		-6		UNITS
	MIN	MAX	MIN	MAX	
t_{RAD} (EDO)	9		12		ns
t_{RAH}	9		10		ns
t_{RAS}	50	10,000	60	10,000	ns
t_{RC} (FPM)	—		110		ns
t_{RC} (EDO)	84		104		ns
t_{RCD} (FPM)	—		20		ns
t_{RCD} (EDO)	11		14		ns
t_{RP}	30		40		ns
t_{RSH}	13		15		ns
t_{RWL}	13		15		ns
t_{WCH}	8		10		ns
t_{WCR}	38		45		ns
t_{WCS}	0		0		ns
t_{WP} (FPM)	—		10		ns
t_{WP} (EDO)	5		5		ns

*EDO version only

FAST-PAGE-MODE READ CYCLE



FAST PAGE MODE TIMING PARAMETERS

SYMBOL	-6		UNITS
	MIN	MAX	
t _{AA}		30	ns
t _{AR}	45		ns
t _{ASC}	0		ns
t _{ASR}	0		ns
t _{CAC}		15	ns
t _{CAH}	10		ns
t _{CAS}	15	10,000	ns
t _{CLZ}	3		ns
t _{CP}	10		ns
t _{CPA}		35	ns
t _{CRP}	5		ns
t _{CSH}	60		ns

SYMBOL	-6		UNITS
	MIN	MAX	
t _{OFF}	3	15	ns
t _{PC}	35		ns
t _{RAC}		60	ns
t _{RAD}	15		ns
t _{RAH}	10		ns
t _{RASP}	60	125,000	ns
t _{RCD}	20		ns
t _{RCH}	0		ns
t _{RCS}	0		ns
t _{RP}	40		ns
t _{RRH}	0		ns
t _{RSH}	15		ns

The diagram illustrates the timing relationships for a memory device. The signals shown are RAS# (Row Address Strobe), CAS# (Column Address Strobe), ADDR (Address), WE# (Write Enable), and DQ (Data Bus). The timing parameters are defined as follows:

- t_{RASP} : RAS pulse width
- t_{CRP} : RAS to CAS delay
- t_{CSH} : CAS setup time
- t_{RCD} : RAS to CAS delay
- t_{CAS} : CAS pulse width
- t_{PC} : Precharge time
- t_{CP} : CAS to Precharge delay
- t_{RSH} : RAS setup time
- t_{RCH} : RAS hold time
- t_{RRH} : RAS to Row Address delay
- t_{AA} : Row Address delay
- t_{CPA} : CAS to Precharge delay
- t_{CAC} : CAS to Column Address delay
- t_{CLZ} : Column Address delay
- t_{COH} : Column Address delay
- t_{OFF} : Column Address delay
- t_{ASR} : Address Setup time
- t_{RAH} : Address Hold time
- t_{ACH} : Address to Column Address delay
- t_{ASC} : Address to Column Address delay
- t_{CAH} : Address to Column Address delay
- t_{RCS} : Row Address delay
- t_{CLZ} : Column Address delay
- t_{AA} : Row Address delay
- t_{CPA} : CAS to Precharge delay
- t_{CAC} : CAS to Column Address delay
- t_{CLZ} : Column Address delay
- t_{COH} : Column Address delay
- t_{OFF} : Column Address delay

The diagram also shows the data bus (DQ) with "VALID DATA" and "OPEN" states. The "DQ" signal is shown with "V_{OH}" and "V_{OL}" levels. The "OPEN" state is indicated by a shaded area. The "VALID DATA" state is indicated by a cross-hatched area. The "DQ" signal is shown with "V_{OH}" and "V_{OL}" levels. The "OPEN" state is indicated by a shaded area. The "VALID DATA" state is indicated by a cross-hatched area.

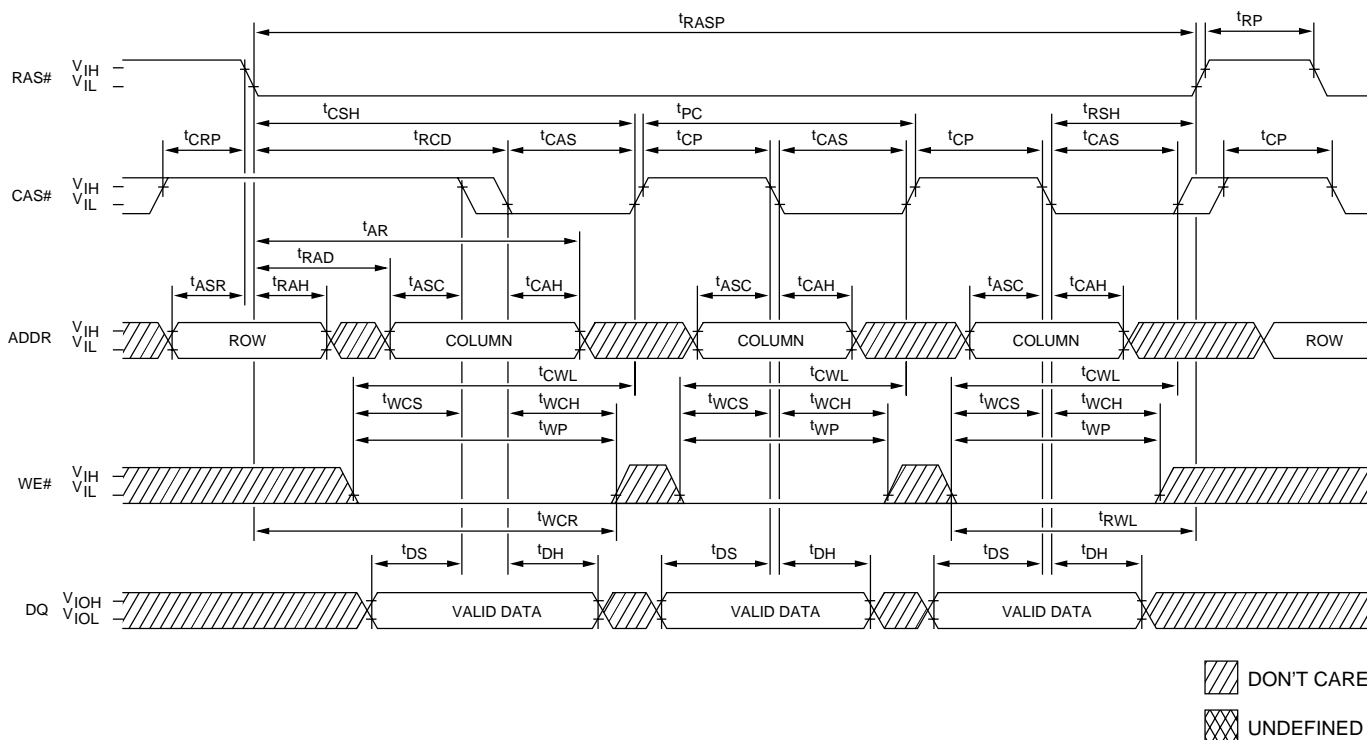
Legend:

- Shaded area: DON'T CARE
- Cross-hatched area: UNDEFINED

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
^t AA		25		30	ns
^t ACH	12		15		ns
^t AR	38		45		ns
^t ASC	0		0		ns
^t ASR	0		0		ns
^t CAC		13		15	ns
^t CAH	8		10		ns
^t CAS	8	10,000	10	10,000	ns
^t CLZ	0		0		ns
^t COH	3		3		ns
^t CP	8		10		ns
^t CPA		28		35	ns
^t CRP	5		5		ns

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
^t CSH	38		45		ns
^t OFF	0	12	0	15	ns
^t PC	20		25		ns
^t RAC		50		60	ns
^t RAD	9		12		ns
^t RAH	9		10		ns
^t RASP	50	125,000	60	125,000	ns
^t RCD	11		14		ns
^t RCH	0		0		ns
^t RCS	0		0		ns
^t RP	30		40		ns
^t RRH	0		0		ns
^t RSH	13		15		ns

FAST-PAGE-MODE EARLY-WRITE CYCLE

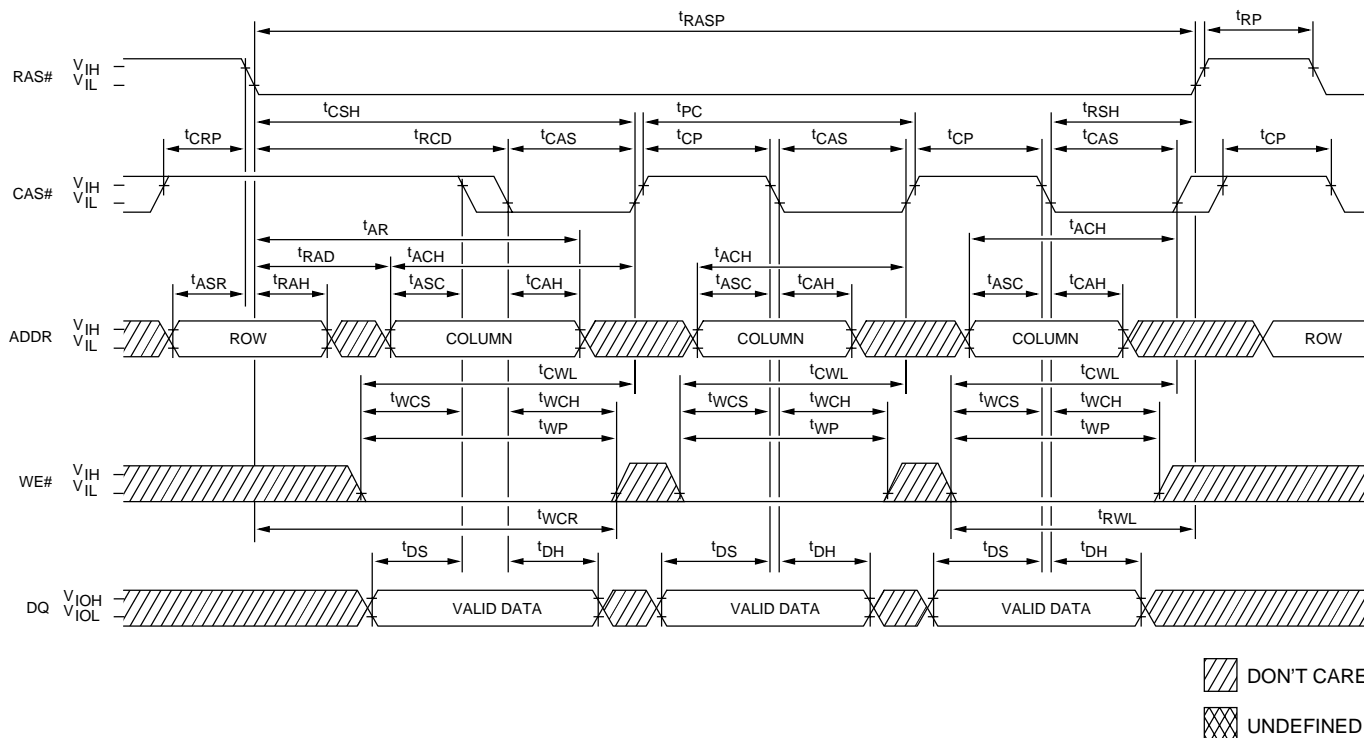


FAST PAGE MODE TIMING PARAMETERS

SYMBOL	-6		UNITS
	MIN	MAX	
t_{AR}	45		ns
t_{ASC}	0		ns
t_{ASR}	0		ns
t_{CAH}	10		ns
t_{CAS}	15	10,000	ns
t_{CP}	10		ns
t_{CRP}	5		ns
t_{CSH}	60		ns
t_{CWL}	15		ns
t_{DH}	10		ns
t_{DS}	0		ns
t_{PC}	35		ns

SYMBOL	-6		UNITS
	MIN	MAX	
t_{RAD}	15		ns
t_{RAH}	10		ns
t_{RASP}	60	125,000	ns
t_{RCD}	20		ns
t_{RP}	40		ns
t_{RSH}	15		ns
t_{RWL}	15		ns
t_{WCH}	10		ns
t_{WCR}	45		ns
t_{WCS}	0		ns
t_{WP}	10		ns

EDO-PAGE-MODE EARLY-WRITE CYCLE

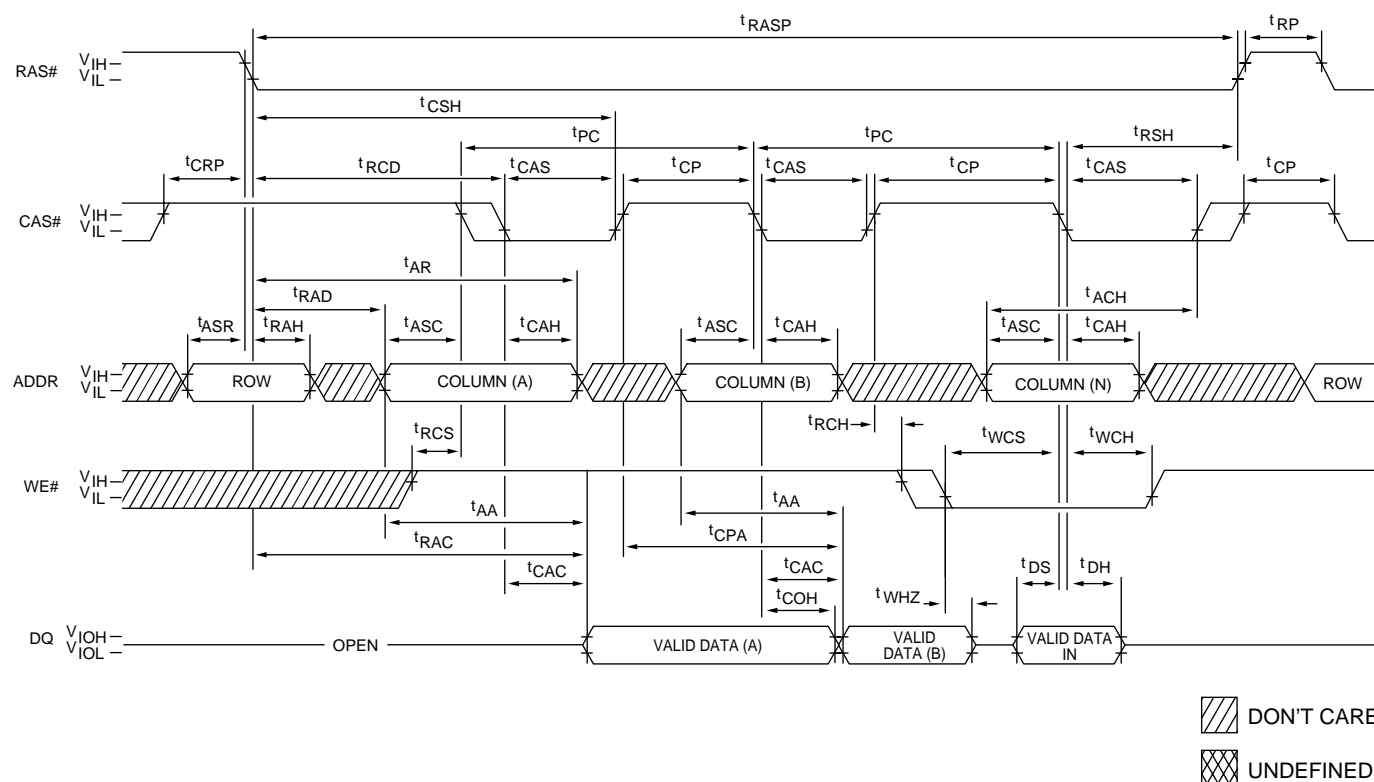


EDO PAGE MODE TIMING PARAMETERS

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{ACH}	12		15		ns
t _{AR}	38		45		ns
t _{ASC}	0		0		ns
t _{ASR}	0		0		ns
t _{CAH}	8		10		ns
t _{CAS}	8	10,000	10	10,000	ns
t _{CP}	8		10		ns
t _{CRP}	5		5		ns
t _{CSH}	38		45		ns
t _{CWL}	8		10		ns
t _{DH}	8		10		ns
t _{DS}	0		0		ns

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{PC}	20		25		ns
t _{RAD}	9		12		ns
t _{RAH}	9		10		ns
t _{RASP}	50	125,000	60	125,000	ns
t _{RCD}	11		14		ns
t _{RP}	30		40		ns
t _{RSH}	13		15		ns
t _{RWL}	13		15		ns
t _{WCH}	8		10		ns
t _{WCR}	38		45		ns
t _{WCS}	0		0		ns
t _{WP}	5		5		ns

EDO-PAGE-MODE READ-EARLY-WRITE CYCLE (Pseudo READ-MODIFY-WRITE)

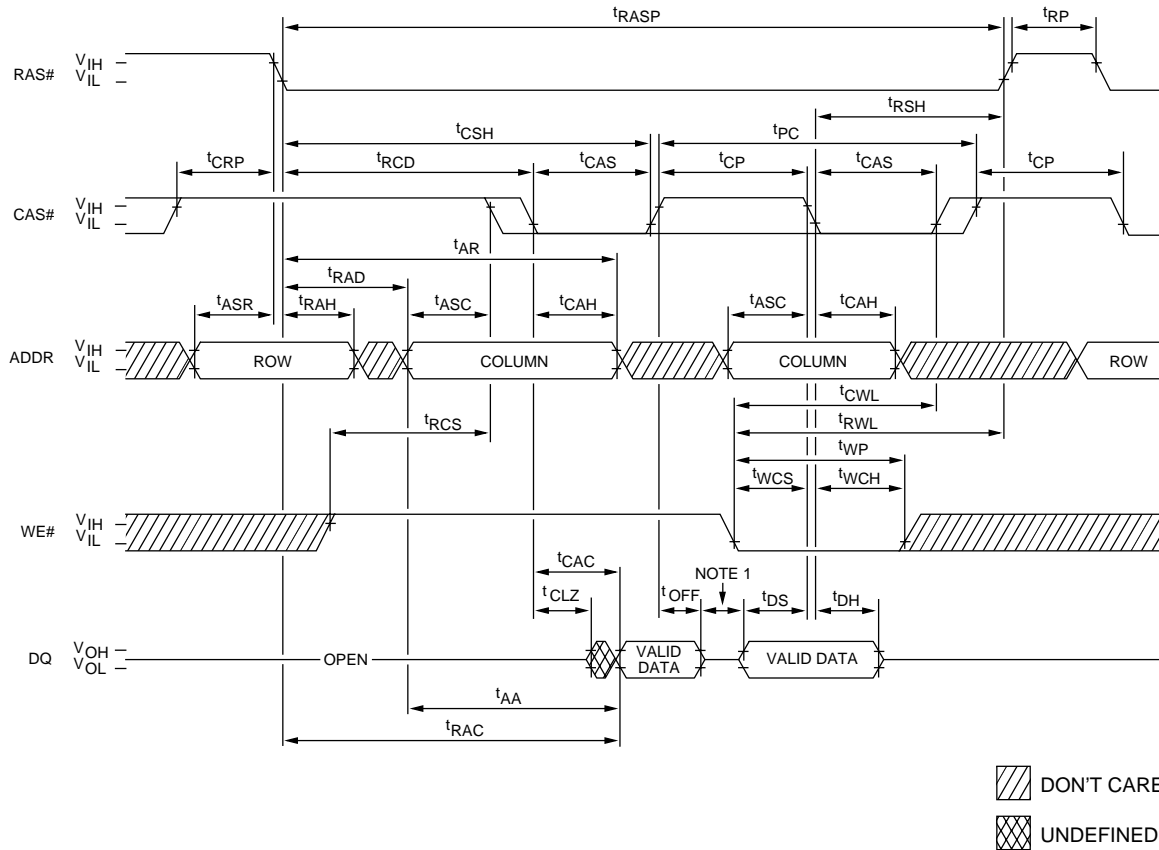


EDO PAGE MODE TIMING PARAMETERS

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{AA}		25		30	ns
t _{ACH}	12		15		ns
t _{AR}	38		45		ns
t _{ASC}	0		0		ns
t _{ASR}	0		0		ns
t _{CAC}		13		15	ns
t _{CAH}	8		10		ns
t _{CAS}	8	10,000	10	10,000	ns
t _{COH}	3		3		ns
t _{CP}	8		10		ns
t _{CPA}		28		35	ns
t _{CRP}	5		5		ns
t _{CSH}	38		45		ns
t _{DH}	8		10		ns

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{DS}	0		0		ns
t _{PC}	20		25		ns
t _{RAC}		50		60	ns
t _{RAD}	9		12		ns
t _{RAH}	9		10		ns
t _{RASP}	50	125,000	60	125,000	ns
t _{RCD}	11		14		ns
t _{RCH}	0		0		ns
t _{RCS}	0		0		ns
t _{RP}	30		40		ns
t _{RSH}	13		15		ns
t _{WCH}	8		10		ns
t _{WCS}	0		0		ns
t _{WHZ}	0	12	0	15	ns

FAST-PAGE-MODE READ-EARLY-WRITE CYCLE (Pseudo READ-MODIFY-WRITE)



DON'T CARE
 UNDEFINED

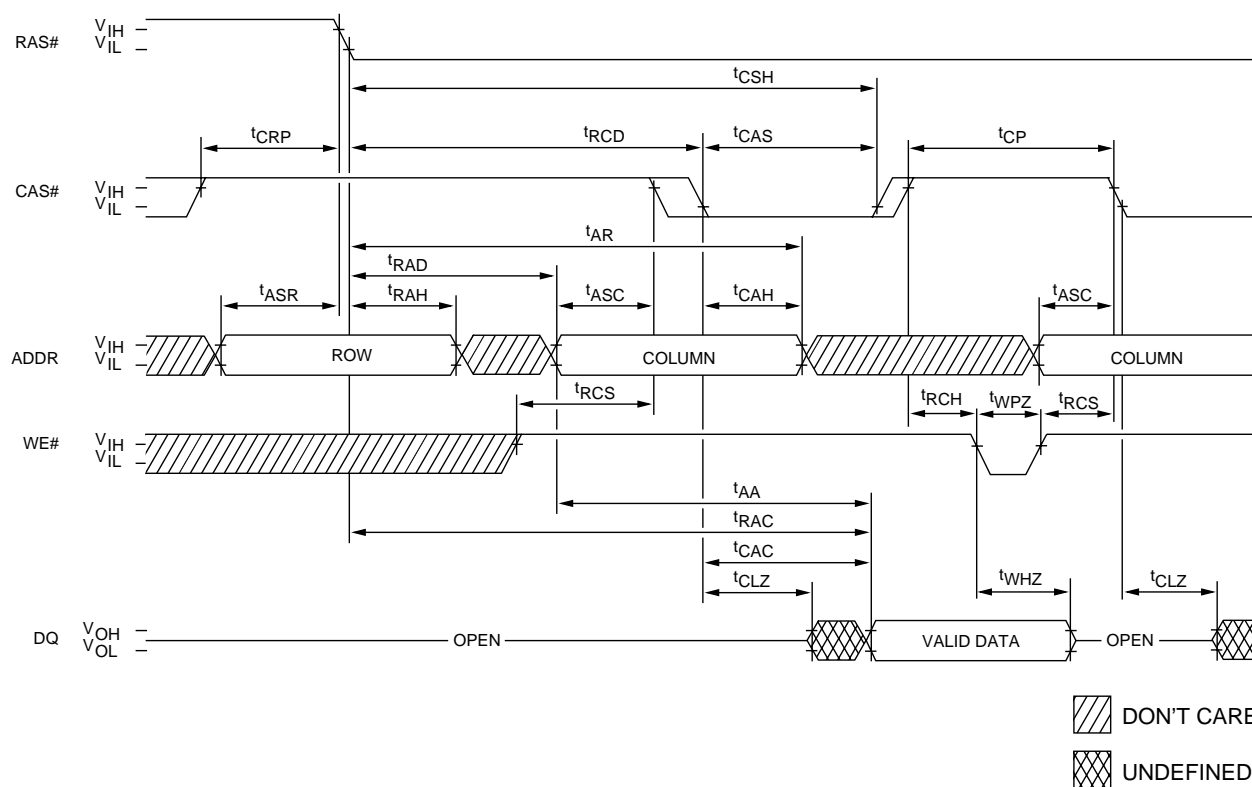
FAST PAGE MODE TIMING PARAMETERS

SYMBOL	-6		UNITS
	MIN	MAX	
t_{AA}		30	ns
t_{AR}	45		ns
t_{ASC}	0		ns
t_{ASR}	0		ns
t_{CAC}		15	ns
t_{CAH}	10		ns
t_{CAS}	15	10,000	ns
t_{CLZ}	3		ns
t_{CP}	10		ns
t_{CRP}	5		ns
t_{CSH}	60		ns
t_{CWL}	15		ns
t_{DH}	10		ns
t_{DS}	0		ns

SYMBOL	-6		UNITS
	MIN	MAX	
t_{OFF}	3	15	ns
t_{PC}	35		ns
t_{RAC}		60	ns
t_{RAD}	15		ns
t_{RAH}	10		ns
t_{RASP}	60	125,000	ns
t_{RCD}	20		ns
t_{RCS}	0		ns
t_{RP}	40		ns
t_{RSH}	15		ns
t_{RWL}	15		ns
t_{WCH}	10		ns
t_{WCS}	0		ns
t_{WP}	10		ns

NOTE: 1. Do not drive data prior to tristate.

EDO READ CYCLE (with WE#-controlled disable)

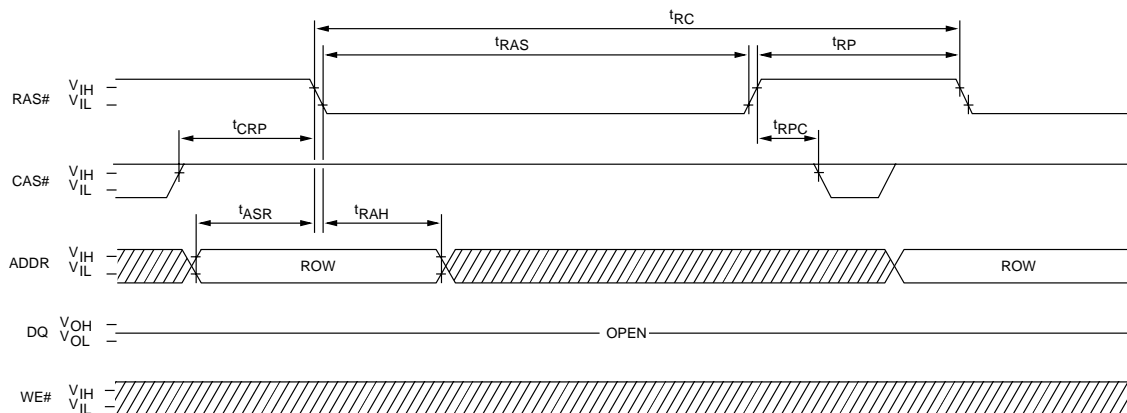


EDO PAGE MODE TIMING PARAMETERS

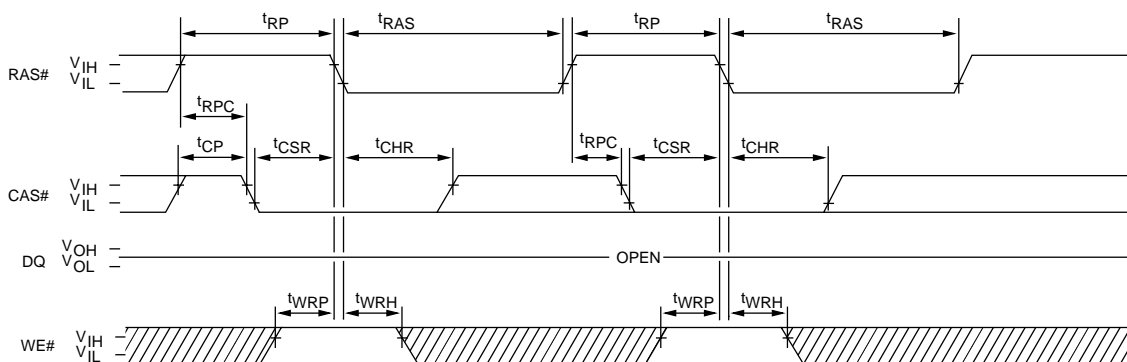
SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{AA}		25		30	ns
t _{AR}	38		45		ns
t _{ASC}	0		0		ns
t _{ASR}	0		0		ns
t _{CAC}		13		15	ns
t _{CAH}	8		10		ns
t _{CAS}	8	10,000	10	10,000	ns
t _{CLZ}	0		0		ns
t _{CP}	8		10		ns
t _{CRP}	5		5		ns

SYMBOL	-5		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{CSH}	38		45		ns
t _{RAC}		50		60	ns
t _{RAD}	9		12		ns
t _{RAH}	9		10		ns
t _{RCD}	11		14		ns
t _{RCH}	0		0		ns
t _{RCS}	0		0		ns
t _{WHZ}	0	12	0	15	ns
t _{WPZ}	10		10		ns

RAS#-ONLY REFRESH CYCLE ²⁵



CBR REFRESH CYCLE ²⁵ (Addresses = DON'T CARE)



DON'T CARE
 UNDEFINED

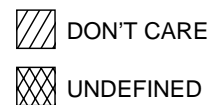
FAST PAGE MODE AND EDO PAGE MODE TIMING PARAMETERS

SYMBOL	-5*		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{ASR}	0		0		ns
t _{CHR} (FPM)	—		10		ns
t _{CHR} (EDO)	8		10		ns
t _{CP}	8		10		ns
t _{CRP}	5		5		ns
t _{CSR}	5		5		ns
t _{RAH}	9		10		ns
t _{RAS}	50	10,000	60	10,000	ns

SYMBOL	-5*		-6		UNITS
	MIN	MAX	MIN	MAX	
t _{RC} (FPM)	—		110		ns
t _{RC} (EDO)	84		104		ns
t _{RP}	30		40		ns
t _{RPC} (FPM)	—		0		ns
t _{RPC} (EDO)	5		5		ns
t _{WRH}	8		10		ns
t _{WRP}	8		10		ns

*EDO version only

(WE# = HIGH)

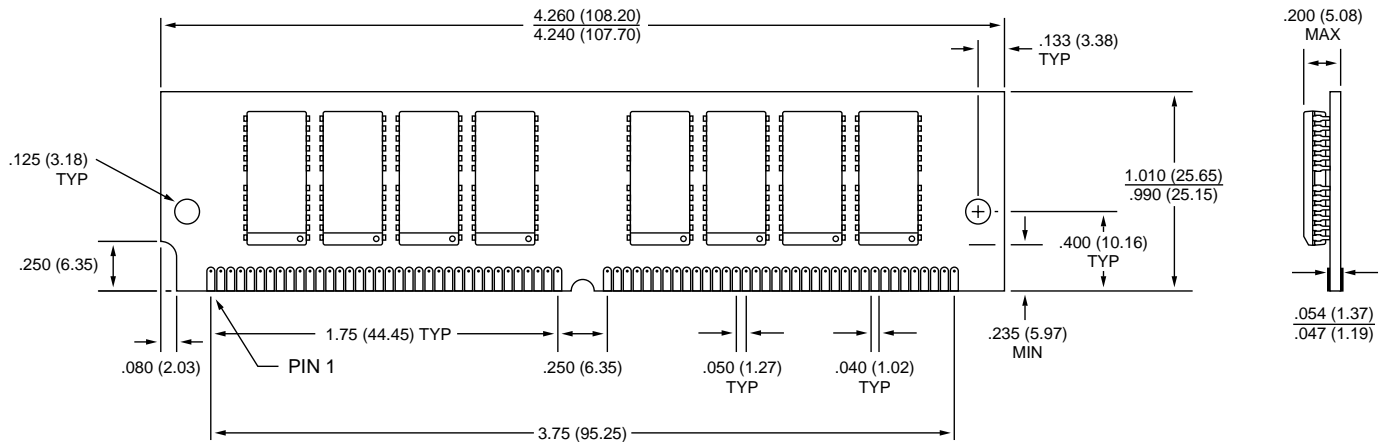


FAST PAGE MODE AND EDO PAGE MODE TIMING PARAMETERS

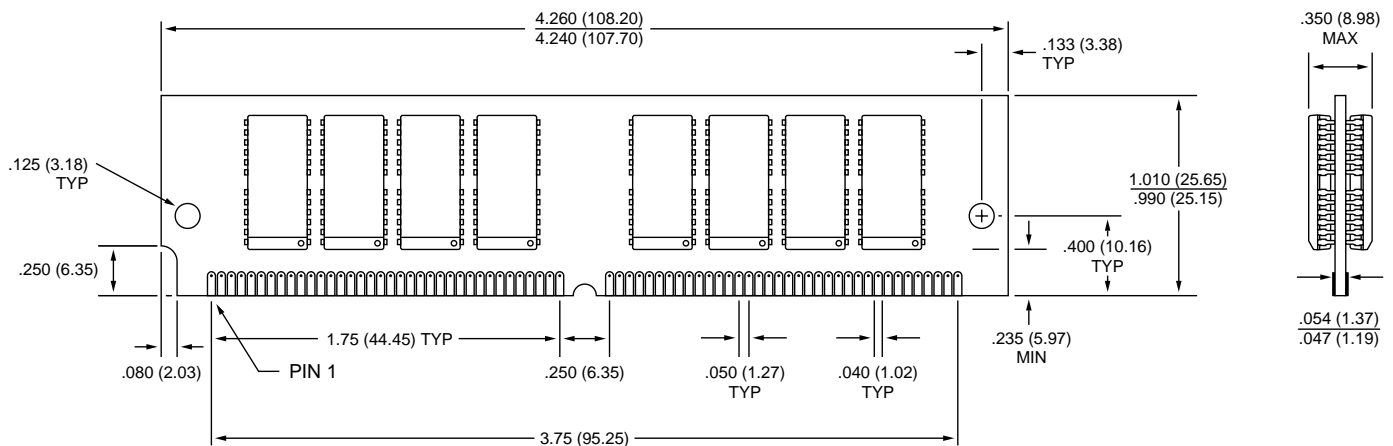
SYMBOL	-5*		-6		UNITS
	MIN	MAX	MIN	MAX	
^t OFF (EDO)	0	12	0	15	ns
^t RAC		50		60	ns
^t RAD (FPM)	—		15		ns
^t RAD (EDO)	9		12		ns
^t RAH	9		10		ns
^t RAS	50	10,000	60	10,000	ns
^t RCD (FPM)	—		20		ns
^t RCD (EDO)	11		14		ns
^t RP	30		40		ns
^t RSH	13		15		ns

*EDO version only

**72-PIN SIMM
DD-3**



**72-PIN SIMM
DD-4**



NOTE: 1. All dimensions in inches (millimeters) $\frac{\text{MAX}}{\text{MIN}}$ or typical where noted.

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